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PTO/SB/08A (10-96)

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Complete if Known

Application Number	10/750,969
Filing Date	01/05/2004
First Named Inventor	Ein-Eli
Group Art Unit	1742
Examiner Name	
Attorney Docket Number	27054

Sheet 1 Of 2

U.S. PATENT DOCUMENTS

Examiners Initials	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD- YYYY	Pages, columns, lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code ² (if known)			
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Examiners Initials	Cite No. ¹	Foreign Patent Documents			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD- YYYY	Pages, columns, lines, Where Relevant Passages or Relevant Figures Appear	1 ⁶
		Office ³	Number ⁴	Kind Code ⁵ (if known)				
Examiner Signature	/Nicholas Smith/					Date Considered	05/08/2007	

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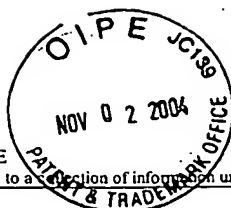
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Sheet	2	Of	2
		Attorney Docket Number	27054
OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial symposium, catalog, etc.) date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
NS		Ein-Eli et al, "Silicon Texturing Under Negative Potential Dissolution (NPD)", <i>Int. Soc. Electrochemistry, Ann. Mtg., Thessaloniki, 19-24-Sept., 2004</i>	
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Examiner Signature	/Nicholas Smith/		Date Considered 05/08/2007

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